

TO-126 Plastic-Encapsulate Transistors

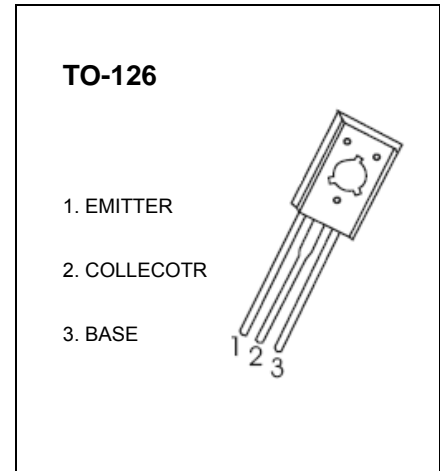
2SC3807 TRANSISTOR (NPN)

FEATURES

- Low frequency power amplifier
- Large current capacity
- High DC current gain
- Low collector-to-emitter saturation voltage
- High V_{EBO}

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Emitter Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	15	V
I_C	Collector Current -Continuous	2	A
P_C	Power dissipation	1.2	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	15			V
Collector cut-off current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 10\text{V}, I_C = 0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE} = 5\text{V}, I_C = 0.5\text{A}$	800		3200	
	h_{FE2}	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	600			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1\text{A}, I_B = 20\text{mA}$			0.5	V
Base-collector saturation voltage	$V_{BE(sat)}$	$I_C = 1\text{A}, I_B = 20\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$		260		MHz
Output capacitance	C_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		27		pF
Turn-on time	t_{on}	$I_C = 0.7\text{A}, I_{B1} = -I_{B2} = 0.1\text{A}$ $V_{CC} = 10\text{V}$		0.14		μs
Storage time	t_{stg}			1.35		μs
Fall time	t_f			0.1		μs